



## JCT825F 25A SCR

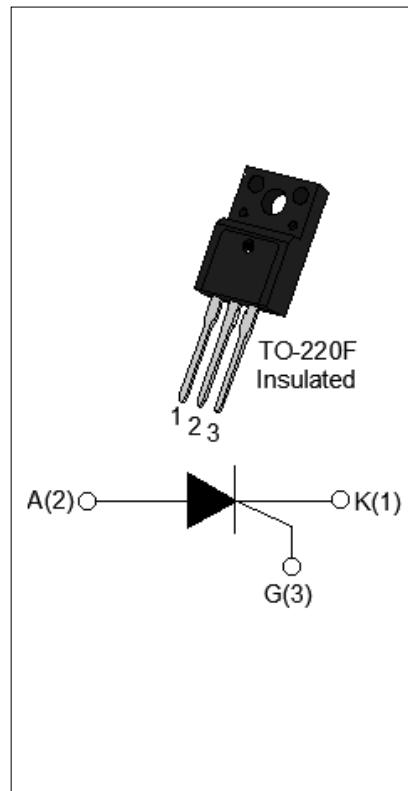
Rev.A.1.0

**DESCRIPTION:**

With high ability to withstand the shock loading of large current, JCT825F SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT825F provides a rated insulation voltage of 2000 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	25	A
V <sub>DRM/V<sub>RRM</sub></sub>	800	V
I <sub>GT</sub>	≤20	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	°C
Operating junction temperature range	T <sub>j</sub>	-40-125	°C
Repetitive peak off-state voltage (T <sub>j</sub> =25°C)	V <sub>DRM</sub>	800	V
Repetitive peak reverse voltage (T <sub>j</sub> =25°C)	V <sub>RRM</sub>	800	V
Average on-state current (T <sub>c</sub> ≤60°C)	I <sub>T(AV)</sub>	16	A
RMS on-state current (T <sub>c</sub> ≤60°C)	I <sub>T(RMS)</sub>	25	A
Non repetitive surge peak on-state current (t <sub>p</sub> =10ms, T <sub>j</sub> =25°C)	I <sub>TSM</sub>	320	A
Non repetitive surge peak on-state current (t <sub>p</sub> =8.3ms, T <sub>j</sub> =25°C)		352	
I <sup>2</sup> t value for fusing (t <sub>p</sub> =10ms, T <sub>j</sub> =25°C)	I <sup>2</sup> t	512	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2×I <sub>GT</sub> , f=100Hz, T <sub>j</sub> =125°C)	dI/dt	200	A/μs

Peak gate current ( $t_p=20\mu s$ , $T_j=125^\circ C$ )	$I_{GM}$	5	A
Average gate power dissipation ( $T_j=125^\circ C$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25^\circ C$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	0.5	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ C$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_L=33\Omega$	-	-	20	mA
$V_{GT}$		-	-	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3K\Omega$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	70	mA
$I_H$	$I_T=500mA$	-	-	60	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=125^\circ C$	1000	-	-	V/ $\mu s$
$t_{on}$	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$	-	2	-	$\mu s$
$t_{off}$		-	50	-	

**STATIC CHARACTERISTICS**

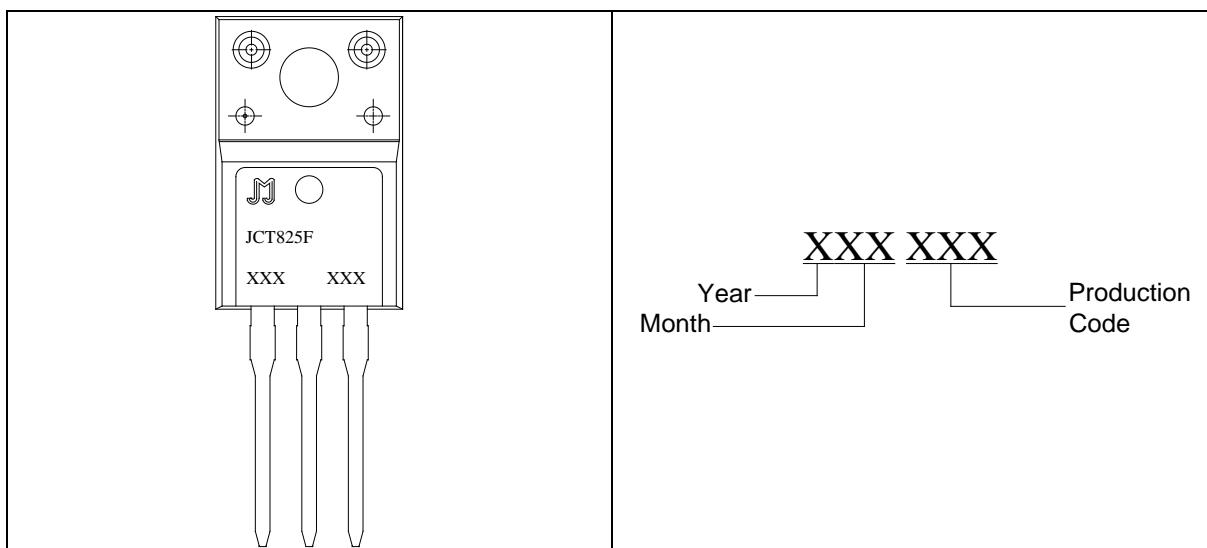
Symbol	Parameter		Value(MAX.)	Unit	
$V_{TM}$	$I_{TM}=50A$	$t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
$V_{TO}$	Threshold voltage		$T_j=125^\circ C$	0.72	V
$R_D$	Dynamic resistance		$T_j=125^\circ C$	16	$m\Omega$
$I_{DRM}$	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ C$	5	$\mu A$
$I_{RRM}$			$T_j=125^\circ C$	0.7	mA

**THERMAL RESISTANCES**

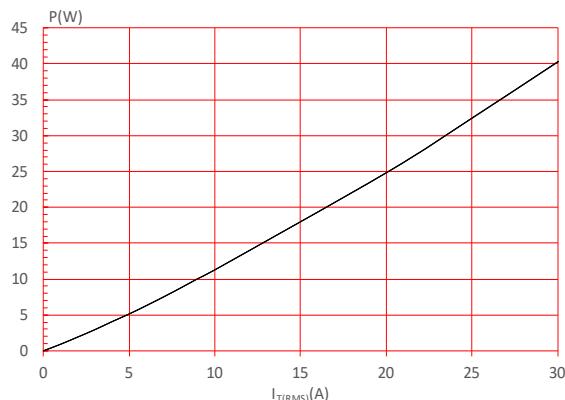
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	2.1	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	62	$^\circ C/W$

**ORDERING INFORMATION**

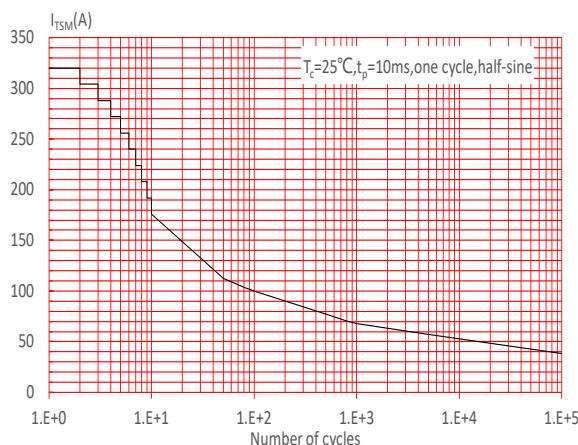
<u>J</u>	<u>CT</u>	<u>8</u>	<u>25</u>	<u>F</u>
<u>JieJie Microelectronics Co.,Ltd.</u>				<u>F:TO-220F(Ins)</u>
	<u>SCRs</u>			
<u>8:V<sub>DRM</sub> /V<sub>RRM</sub> ≥800V</u>			<u>I<sub>T(RMS)</sub>:25A</u>	

**MARKING**

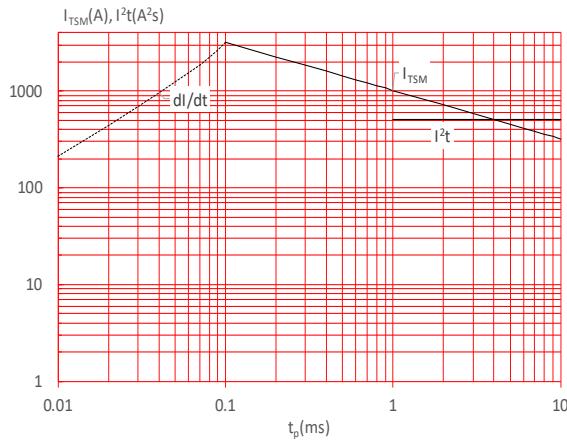
**FIG.1** Maximum power dissipation versus RMS on-state current



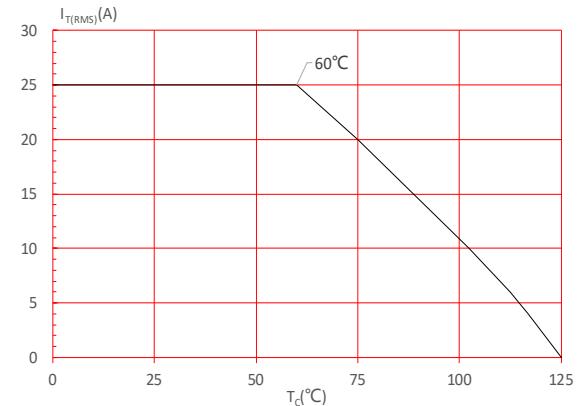
**FIG.3:** Surge peak on-state current versus number of cycles



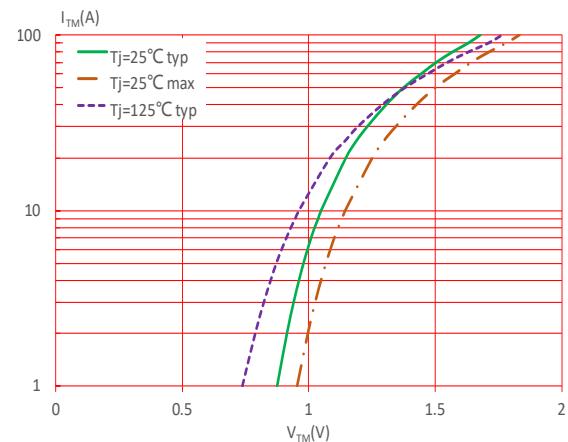
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 200\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

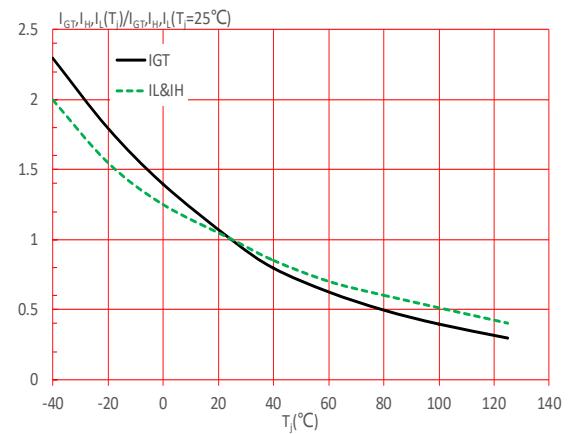
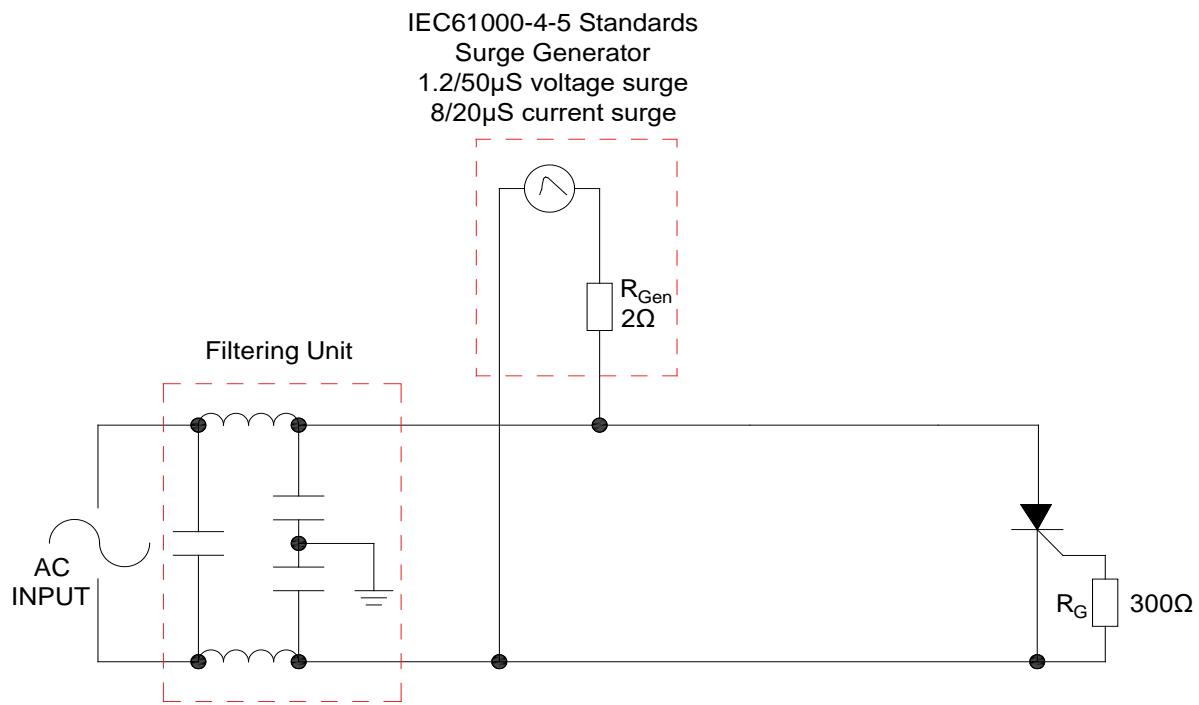


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

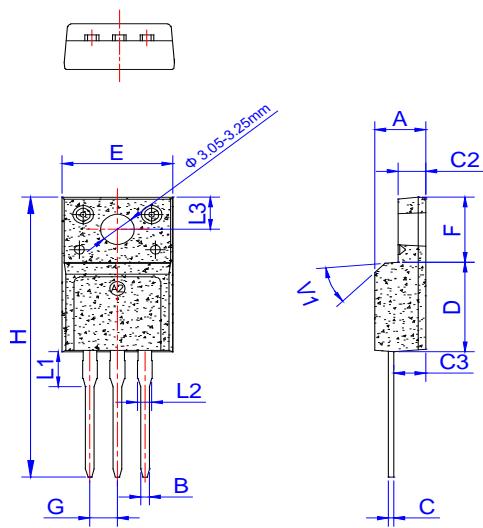
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT825F	800	20	TO-220F(Ins)	50	Tube

**Document Revision History**

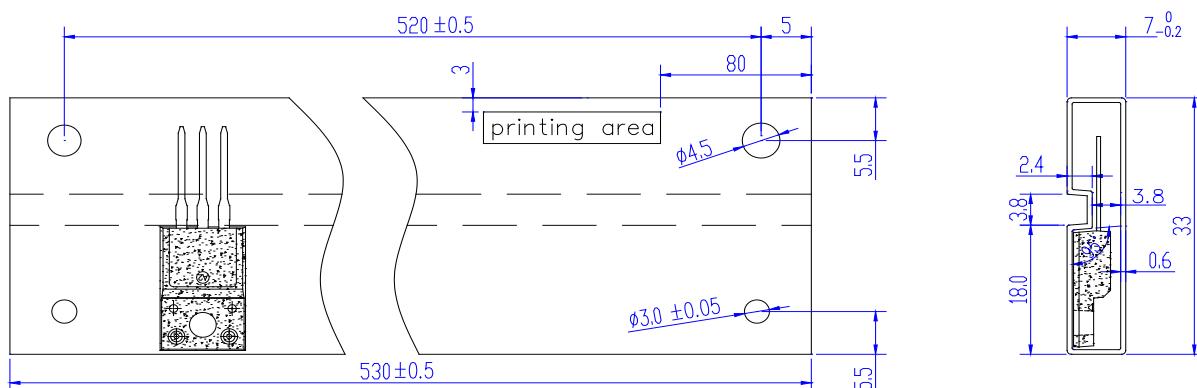
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		$45^\circ$			$45^\circ$	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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